



Welcome to **E-XFL.COM**

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	25MHz
Connectivity	I ² C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	48KB (24K x 16)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	3.8K x 8
Voltage - Supply (Vcc/Vdd)	4.2V ~ 5.5V
Data Converters	A/D 13x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Through Hole
Package / Case	40-DIP (0.600", 15.24mm)
Supplier Device Package	40-PDIP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18f4515-e-p

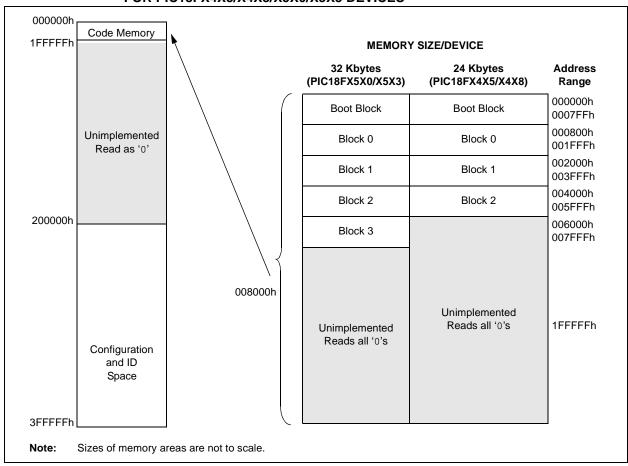
Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

TABLE 2-4: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F2455	
PIC18F2458	000000h 005FFFh (24K)
PIC18F4455	000000h-005FFFh (24K)
PIC18F4458	
PIC18F2510	
PIC18F2520	
PIC18F2523	
PIC18F2550	
PIC18F2553	000000h 007FFFh (20K)
PIC18F4510	000000h-007FFFh (32K)
PIC18F4520	
PIC18F4523	
PIC18F4550	
PIC18F4553	

FIGURE 2-8: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX4X5/X4X8/X5X0/X5X3 DEVICES

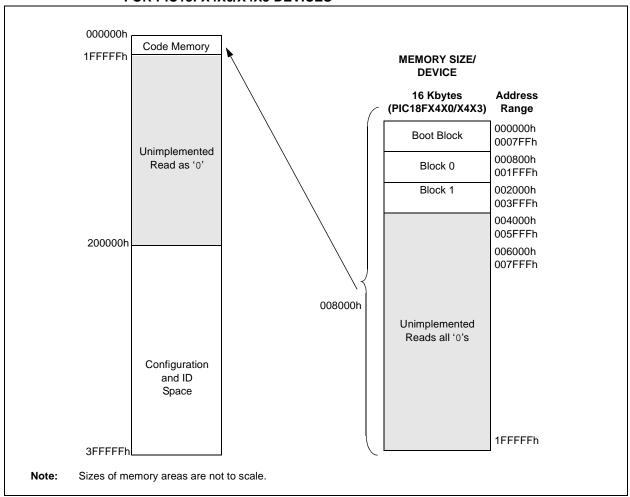


For PIC18FX4X0/X4X3 devices, the code memory space extends from 000000h to 003FFh (16 Kbytes) in two 8-Kbyte blocks. Addresses, 000000h through 0003FFh, however, define a "Boot Block" region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-5: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F2410	
PIC18F2420	
PIC18F2423	
PIC18F2450	000000h-003FFFh (16K)
PIC18F4410	
PIC18F4420]
PIC18F4450	

FIGURE 2-9: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX4X0/X4X3 DEVICES



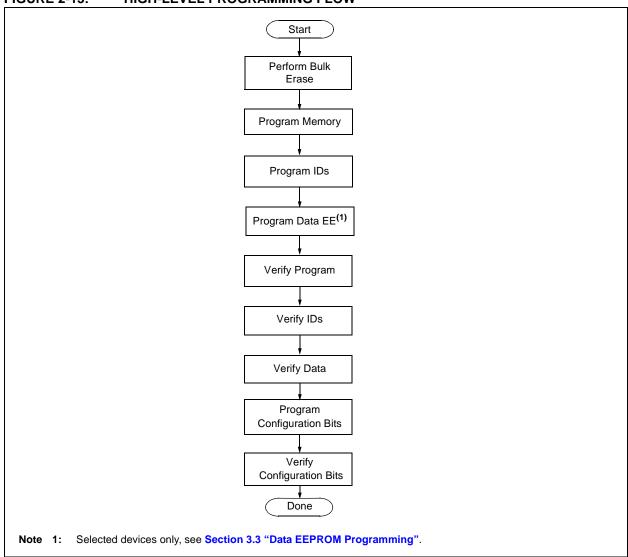
For PIC18F2480/4480 devices, the code memory space extends from 0000h to 03FFFh (16 Kbytes) in one 16-Kbyte block. For PIC18F2580/4580 devices, the code memory space extends from 0000h to 07FFFh (32 Kbytes) in two 16-Kbyte blocks. Addresses, 0000h through 07FFh, however, define a "Boot Block" region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

The size of the Boot Block in PIC18F2480/2580/4480/4580 devices can be configured as 1 or 2K words (see Figure 2-10). This is done through the BBSIZ<0> bit in the Configuration register, CONFIG4L. It is important to note that increasing the size of the Boot Block decreases the size of Block 0.

2.4 High-Level Overview of the Programming Process

Figure 2-13 shows the high-level overview of the programming process. First, a Bulk Erase is performed. Next, the code memory, ID locations and data EEPROM are programmed (selected devices only, see **Section 3.3 "Data EEPROM Programming"**). These memories are then verified to ensure that programming was successful. If no errors are detected, the Configuration bits are then programmed and verified.

FIGURE 2-13: HIGH-LEVEL PROGRAMMING FLOW

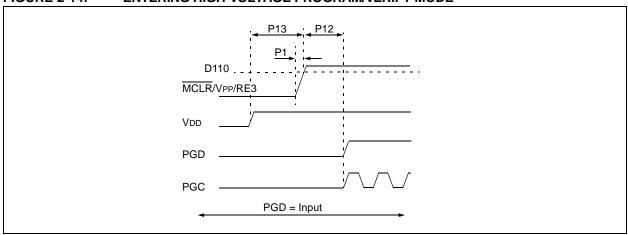


2.5 Entering and Exiting High-Voltage ICSP Program/Verify Mode

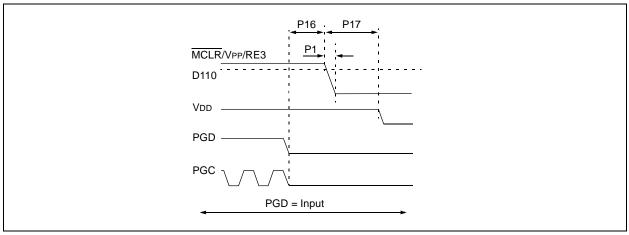
As shown in Figure 2-14, the High-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low and then raising MCLR/VPP/RE3 to VIHH (high voltage). Once in this mode, the code memory, data EEPROM (selected devices only, see **Section 3.3 "Data EEPROM Programming"**), ID locations and Configuration bits can be accessed and programmed in serial fashion. Figure 2-15 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-14: ENTERING HIGH-VOLTAGE PROGRAM/VERIFY MODE







2.8 Dedicated ICSP/ICD Port (44-Pin TQFP Only)

The PIC18F4455/4458/4550/4553 44-pin TQFP devices are designed to support an alternate programming input: the dedicated ICSP/ICD port. The primary purpose of this port is to provide an alternate In-Circuit Debugging (ICD) option and free the pins (RB6, RB7 and \overline{MCLR}) that would normally be used for debugging the application. In conjunction with ICD capability, however, the dedicated ICSP/ICD port also provides an alternate port for ICSP.

Setting the ICPRT Configuration bit enables the dedicated ICSP/ICD port. The dedicated ICSP/ICD port functions the same as the default ICSP/ICD port; however, alternate pins are used instead of the default pins. Table 2-10 identifies the functionally equivalent pins for ICSP purposes:

The dedicated ICSP/ICD port is an alternate port. Thus, ICSP is still available through the default port even though the ICPRT Configuration bit is set. When the VIH is seen on the MCLR/VPP/RE3 pin prior to applying VIH to the ICRST/ICVPP pin, then the state of the ICRST/ICVPP pin is ignored. Likewise, when the VIH is seen on ICRST/ICVPP prior to applying VIH to MCLR/VPP/RE3, then the state of the MCLR/VPP/RE3 pin is ignored.

Note: The ICPRT Configuration bit can only be programmed through the default ICSP port. Chip Erase functions through the dedicated ICSP/ICD port do not affect this bit.

When the ICPRT Configuration bit is set (dedicated ICSP/ICD port enabled), the NC/ICPORTS pin must be tied to either VDD or VSS.

The ICPRT Configuration bit must be maintained clear for all 28-pin and 40-pin devices; otherwise, unexpected operation may occur.

TABLE 2-10: ICSP™ EQUIVALENT PINS

Pin Name	During Programming						
Pili Name	Pin Name	Pin Type	Dedicated Pins	Pin Description			
MCLR/Vpp/RE3	VPP	Р	NC/ICRST/ICVPP	Programming Enable			
RB6	PGC	I	NC/ICCK/ICPGC	Serial Clock			
RB7	PGD	I/O	NC/ICDT/ICPGD	Serial Data			

Legend: I = Input, O = Output, P = Power

3.0 DEVICE PROGRAMMING

Programming includes the ability to erase or write the various memory regions within the device.

In all cases, except high-voltage ICSP Bulk Erase, the EECON1 register must be configured in order to operate on a particular memory region.

When using the EECON1 register to act on code memory, the EEPGD bit must be set (EECON1<7> = 1) and the CFGS bit must be cleared (EECON1<6> = 0). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort (e.g., erases) and this must be done prior to initiating a write sequence. The FREE bit must be set (EECON1<4> = 1) in order to erase the program space being pointed to by the Table Pointer. The erase or write sequence is initiated by setting the WR bit (EECON1<1> = 1). It is strongly recommended that the WREN bit only be set immediately prior to a program erase.

3.1 ICSP Erase

3.1.1 HIGH-VOLTAGE ICSP BULK ERASE

Erasing code or data EEPROM is accomplished by configuring two Bulk Erase Control registers located at 3C0004h and 3C0005h. Code memory may be erased, portions at a time, or the user may erase the entire device in one action. Bulk Erase operations will also clear any code-protect settings associated with the memory block being erased. Erase options are detailed in Table 3-1. If data EEPROM is code-protected (CPD = 0), the user must request an erase of data EEPROM (e.g., 0084h as shown in Table 3-1).

TABLE 3-1: BULK ERASE OPTIONS

Description	Data (3C0005h:3C0004h)			
Chip Erase	3F8Fh			
Erase Data EEPROM ⁽¹⁾	0084h			
Erase Boot Block	0081h			
Erase Configuration Bits	0082h			
Erase Code EEPROM Block 0	0180h			
Erase Code EEPROM Block 1	0280h			
Erase Code EEPROM Block 2	0480h			
Erase Code EEPROM Block 3	0880h			
Erase Code EEPROM Block 4	1080h			
Erase Code EEPROM Block 5	2080h			

Note 1: Selected devices only, see Section 3.3 "Data EEPROM Programming".

The actual Bulk Erase function is a self-timed operation. Once the erase has started (falling edge of the 4th PGC after the NOP command), serial execution will cease until the erase completes (Parameter P11). During this time, PGC may continue to toggle but PGD must be held low.

The code sequence to erase the entire device is shown in Table and the flowchart is shown in Figure 3-1.

Note: A Bulk Erase is the only way to reprogram code-protect bits from an ON state to an OFF state.

TABLE 3-2: BULK ERASE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 05	MOVLW 05h
0000	6E F6	MOVWF TBLPTRL
1100	3F 3F	Write 3F3Fh to 3C0005h
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 04	MOVLW 04h
0000	6E F6	MOVWF TBLPTRL
1100	8F 8F	Write 8F8Fh TO 3C0004h to erase entire device.
		NOP
		Hold PGD low until erase completes.
0000	00 00	
0000	00 00	

FIGURE 3-1: BULK ERASE FLOW

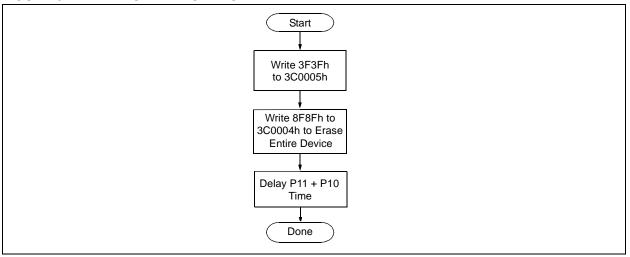
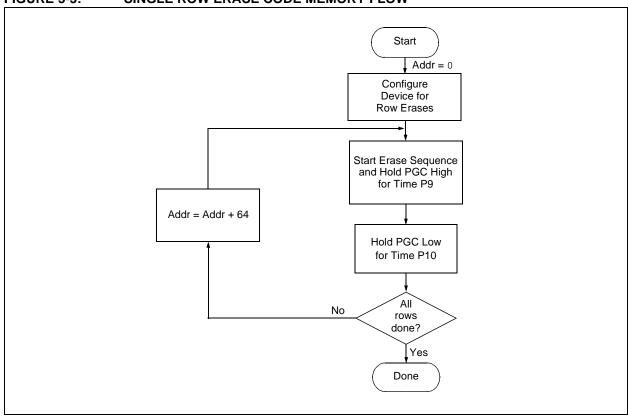


TABLE 3-3: ERASE CODE MEMORY CODE SEQUENCE

Step 1: Direct access to code memory and enable writes. 0000 8E A6 BSF EECON1, EEPGD 0000 9C A6 BCF EECON1, CFGS 0000 84 A6 BSF EECON1, WREN Step 2: Point to first row in code memory. 0000 6A F8 CLRF TBLPTRU 0000 6A F7 CLRF TBLPTRH 0000 6A F6 CLRF TBLPTRL Step 3: Enable erase and erase single row. 0000 88 A6 BSF EECON1, FREE 0000 82 A6 BSF EECON1, WR 0000 00 00 NOP - hold PGC high for time P9 and low for time P10.	4-Bit Command	Data Payload	Core Instruction						
0000 9C A6 BCF EECON1, CFGS 0000 84 A6 BSF EECON1, WREN Step 2: Point to first row in code memory. 0000 6A F8 CLRF TBLPTRU 0000 6A F7 CLRF TBLPTRH 0000 6A F6 CLRF TBLPTRL Step 3: Enable erase and erase single row. 0000 88 A6 BSF EECON1, FREE 0000 82 A6 BSF EECON1, WR	Step 1: Direct ac	Step 1: Direct access to code memory and enable writes.							
0000 6A F8 CLRF TBLPTRU 0000 6A F7 CLRF TBLPTRH 0000 6A F6 CLRF TBLPTRL Step 3: Enable erase and erase single row. 0000 88 A6 BSF EECON1, FREE 0000 82 A6 BSF EECON1, WR	0000	0000 9C A6 BCF EECON1, CFGS							
0000 6A F7 CLRF TBLPTRH 0000 6A F6 CLRF TBLPTRL Step 3: Enable erase and erase single row. 0000 88 A6 BSF EECON1, FREE 0000 82 A6 BSF EECON1, WR	Step 2: Point to f	irst row in code memory.							
0000 88 A6 BSF EECON1, FREE 0000 82 A6 BSF EECON1, WR	0000	6A F7	CLRF TBLPTRH						
0000 82 A6 BSF EECON1, WR	Step 3: Enable e	rase and erase single ro	w.						
	0000 82 A6 BSF EECON1, WR								

FIGURE 3-3: SINGLE ROW ERASE CODE MEMORY FLOW



3.2 Code Memory Programming

Programming code memory is accomplished by first loading data into the write buffer and then initiating a programming sequence. The write and erase buffer sizes, shown in Table 3-4, can be mapped to any location of the same size, beginning at 000000h. The actual memory write sequence takes the contents of this buffer and programs the proper amount of code memory that contains the Table Pointer.

The programming duration is externally timed and is controlled by PGC. After a Start Programming command is issued (4-bit command, '1111'), a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to program a PIC18F2XXX/4XXX Family device is shown in Table 3-5. The flowchart, shown in Figure 3-4, depicts the logic necessary to completely write a PIC18F2XXX/4XXX Family device. The timing diagram that details the Start Programming command and Parameters P9 and P10 is shown in Figure 3-5.

Note: The TBLPTR register must point to the same region when initiating the programming sequence as it did when the write buffers were loaded.

TABLE 3-4: WRITE AND ERASE BUFFER SIZES

Devices (Arranged by Family)	Write Buffer Size (Bytes)	Erase Buffer Size (Bytes)	
PIC18F2221, PIC18F2321, PIC18F4221, PIC18F4321	8	64	
PIC18F2450, PIC18F4450	16	64	
PIC18F2410, PIC18F2510, PIC18F4410, PIC18F4510			
PIC18F2420, PIC18F2520, PIC18F4420, PIC18F4520			
PIC18F2423, PIC18F2523, PIC18F4423, PIC18F4523	32	64	
PIC18F2480, PIC18F2580, PIC18F4480, PIC18F4580	32		
PIC18F2455, PIC18F2550, PIC18F4455, PIC18F4550			
PIC18F2458, PIC18F2553, PIC18F4458, PIC18F4553			
PIC18F2515, PIC18F2610, PIC18F4515, PIC18F4610			
PIC18F2525, PIC18F2620, PIC18F4525, PIC18F4620	64	64	
PIC18F2585, PIC18F2680, PIC18F4585, PIC18F4680	- 64		
PIC18F2682, PIC18F2685, PIC18F4682, PIC18F4685			

TABLE 3-5: WRITE CODE MEMORY CODE SEQUENCE

4-Bit Command	Data Payload	Core Instruction					
Step 1: Direct acc	Step 1: Direct access to code memory and enable writes.						
0000	8E A6 9C A6	BSF EECON1, EEPGD BCF EECON1, CFGS					
Step 2: Load write	e buffer.						
0000 0000 0000 0000 0000	0E <addr[21:16]> 6E F8 0E <addr[15:8]> 6E F7 0E <addr[7:0]> 6E F6</addr[7:0]></addr[15:8]></addr[21:16]>	MOVLW <addr[21:16]> MOVWF TBLPTRU MOVLW <addr[15:8]> MOVWF TBLPTRH MOVLW <addr[7:0]> MOVWF TBLPTRL</addr[7:0]></addr[15:8]></addr[21:16]>					
Step 3: Repeat for	r all but the last two byte	es.					
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.					
Step 4: Load write	Step 4: Load write buffer for last two bytes.						
1111 0000	<msb><lsb></lsb></msb>	Write 2 bytes and start programming. NOP - hold PGC high for time P9 and low for time P10.					
To continue writing data, repeat Steps 2 through 4, where the Address Pointer is incremented by 2 at each iteration of the loop.							

FIGURE 3-4: PROGRAM CODE MEMORY FLOW

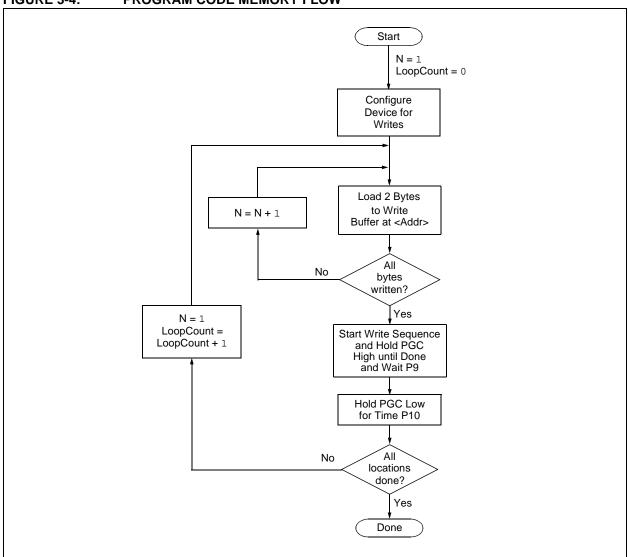
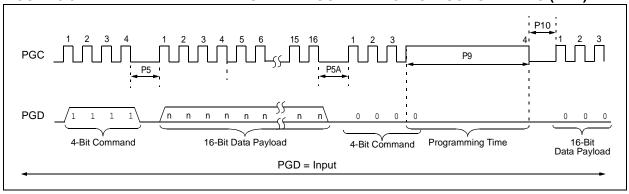


FIGURE 3-5: TABLE WRITE AND START PROGRAMMING INSTRUCTION TIMING (1111)



3.3 Data EEPROM Programming

Note: Data EEPROM programming is not available or	Data EEPROM programming is not available on the following devices:						
PIC18F2410	PIC18F4410						
PIC18F2450	PIC18F4450						
PIC18F2510	PIC18F4510						
PIC18F2515	PIC18F4515						
PIC18F2610	PIC18F4610						

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair: EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADRH:EEADR with the desired memory location, EEDATA, with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared (EECON1<7:6> = 00). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit (EECON1<1> = 1).

The write begins on the falling edge of the 4th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must still be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

FIGURE 3-6: PROGRAM DATA FLOW

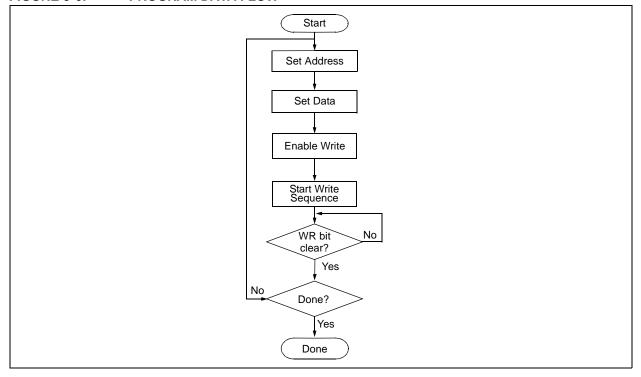
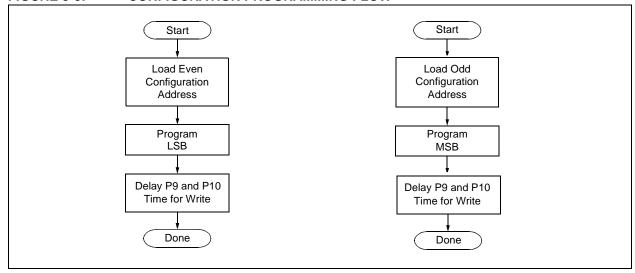


TABLE 3-9: SET ADDRESS POINTER TO CONFIGURATION LOCATION

4-Bit Command	Data Payload	Core Instruction
Step 1: Enable wr	ites and direct access to cor	nfiguration memory.
0000	8E A6 8C A6	BSF EECON1, EEPGD BSF EECON1, CFGS
		e to be written. Write even/odd addresses. ⁽¹⁾
0000	0E 30	MOVLW 30h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPRTH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1111	<msb ignored=""><lsb></lsb></msb>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
0000	0E 01	MOVLW 01h
0000	6E F6	MOVWF TBLPTRL
1111	<msb><lsb ignored=""></lsb></msb>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.

Note 1: Enabling the write protection of Configuration bits (WRTC = 0 in CONFIG6H) will prevent further writing of the Configuration bits. Always write all the Configuration bits before enabling the write protection for Configuration bits.

FIGURE 3-8: CONFIGURATION PROGRAMMING FLOW



4.2 Verify Code Memory and ID Locations

The verify step involves reading back the code memory space and comparing it against the copy held in the programmer's buffer. Memory reads occur a single byte at a time, so two bytes must be read to compare against the word in the programmer's buffer. Refer to **Section 4.1** "**Read Code Memory, ID Locations and Configuration Bits**" for implementation details of reading code memory.

The Table Pointer must be manually set to 200000h (base address of the ID locations) once the code memory has been verified. The post-increment feature of the Table Read 4-bit command may not be used to increment the Table Pointer beyond the code memory space. In a 64-Kbyte device, for example, a post-increment read of address, FFFFh, will wrap the Table Pointer back to 000000h, rather than point to the unimplemented address, 010000h.

Start Set TBLPTR = 200000h Set TBLPTR = 0 Read Low Byte Read Low Byte with Post-Increment with Post-Increment Read High Byte Increment Read High Byte with Post-Increment Pointer with Post-Increment Does Does No Word = Expect Failure, Word = Expect Failure, Data? Report Data? Report Error Error Yes Yes ΑII No No **ID** locations code memory verified? verified? Yes Yes Done

FIGURE 4-2: VERIFY CODE MEMORY FLOW

4.3 Verify Configuration Bits

A configuration address may be read and output on PGD via the 4-bit command, '1001'. Configuration data is read and written in a byte-wise fashion, so it is not necessary to merge two bytes into a word prior to a compare. The result may then be immediately compared to the appropriate configuration data in the programmer's memory for verification. Refer to **Section 4.1 "Read Code Memory, ID Locations and Configuration Bits"** for implementation details of reading configuration data.

TABLE 5-1: CONFIGURATION BITS AND DEVICE IDS

File N	lame	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Default/ Unprogrammed Value
300000h ^(1,8)	CONFIG1L	_	-	USBDIV	CPUDIV1	CPUDIV0	PLLDIV2	PLLDIV1	PLLDIV0	00 0000
300001h	CONFIG1H	IESO	FCMEN	_	_	FOSC3	FOSC2	FOSC1	FOSC0	00 0111
										00 0101 ^(1,8)
300002h	CONFIG2L	_	_	VREGEN ^(1,8)	BORV1	BORV0	BOREN1	BOREN0	PWRTEN	1 1111 01 1111 ^(1,8)
300003h	CONFIG2H			- VREGEN	WDTPS3	WDTPS2	WDTPS1	WDTPS0	WDTEN	1 1111
-									CCP2MX ⁽⁷⁾	1011(7)
300005h	CONFIG3H	MCLRE	_	_	_	_	LPT1OSC	PBADEN	_	101-
				ICPRT ⁽¹⁾	_	_				1001-1(1)
		G4L DEBUG	UG XINST	BBSIZ1	BBSIZ0	-	LVP -			1000 -1-1
300006h	006h CONFIG4L DEBU			_	BBSIZ ⁽³⁾	_		_	STVREN	10-0 -1-1(3)
				ICPRT ⁽⁸⁾	_	BBSIZ ⁽⁸⁾				100- 01-1(8)
				BBSIZ1 ⁽²⁾	BBSIZ2 ⁽²⁾	ı				1000 -1-1 (2)
300008h	CONFIG5L	_	-	CP5 ⁽¹⁰⁾	CP4 ⁽⁹⁾	CP3 ⁽⁴⁾	CP2 ⁽⁴⁾	CP1	CP0	11 1111
300009h	CONFIG5H	CPD	СРВ	l	_	I	-	I		11
30000Ah	CONFIG6L	_		WRT5 ⁽¹⁰⁾	WRT4 ⁽⁹⁾	WRT3 ⁽⁴⁾	WRT2 ⁽⁴⁾	WRT1	WRT0	11 1111
30000Bh	CONFIG6H	WRTD	WRTB	WRTC ⁽⁵⁾	_	_	_	_		111
30000Ch	CONFIG7L	_	_	EBTR5 ⁽¹⁰⁾	EBTR4 ⁽⁹⁾	EBTR3 ⁽⁴⁾	EBTR2 ⁽⁴⁾	EBTR1	EBTR0	11 1111
30000Dh	CONFIG7H	_	EBTRB	-	_	-		_	_	-1
3FFFFEh	DEVID1 ⁽⁶⁾	DEV2	DEV1	DEV0	REV4	REV3	REV2	REV1	REV0	See Table 5-2
3FFFFFh	DEVID2 ⁽⁶⁾	DEV10	DEV9	DEV8	DEV7	DEV6	DEV5	DEV4	DEV3	See Table 5-2

Legend: - = unimplemented. Shaded cells are unimplemented, read as '0'.

- Note 1: Implemented only on PIC18F2455/2550/4455/4550 and PIC18F2458/2553/4458/4553 devices.
 - 2: Implemented on PIC18F2585/2680/4585/4680, PIC18F2682/2685 and PIC18F4682/4685 devices only.
 - 3: Implemented on PIC18F2480/2580/4480/4580 devices only.
 - 4: These bits are only implemented on specific devices based on available memory. Refer to Section 2.3 "Memory Maps".
 - 5: In PIC18F2480/2580/4480/4580 devices, this bit is read-only in Normal Execution mode; it can be written only in Program mode.
 - **6:** DEVID registers are read-only and cannot be programmed by the user.
 - 7: Implemented on all devices with the exception of the PIC18FXX8X and PIC18F2450/4450 devices.
 - 8: Implemented on PIC18F2450/4450 devices only.
 - 9: Implemented on PIC18F2682/2685 and PIC18F4682/4685 devices only.
 - 10: Implemented on PIC18F2685/4685 devices only.

TABLE 5-2: DEVICE ID VALUES (CONTINUED)

Device	Device ID Value					
Device	DEVID2	DEVID1				
PIC18F4585	0Eh	101x xxxx				
PIC18F4610	0Ch	001x xxxx				
PIC18F4620	0Ch	000x xxxx				
PIC18F4680	0Eh	100x xxxx				
PIC18F4682	27h	010x xxxx				
PIC18F4685	27h	011x xxxx				

Legend: The 'x's in DEVID1 contain the device revision code.

Note 1: DEVID1 bit 4 is used to determine the device type (REV4 = 0).

2: DEVID1 bit 4 is used to determine the device type (REV4 = 1).

TABLE 5-3: PIC18F2XXX/4XXX FAMILY BIT DESCRIPTIONS

Bit Name	Configuration Words	Description
IESO	CONFIG1H	Internal External Switchover bit 1 = Internal External Switchover mode is enabled 0 = Internal External Switchover mode is disabled
FCMEN	CONFIG1H	Fail-Safe Clock Monitor Enable bit 1 = Fail-Safe Clock Monitor is enabled 0 = Fail-Safe Clock Monitor is disabled
FOSC<3:0>	CONFIG1H	Oscillator Selection bits 11xx = External RC oscillator, CLKO function on RA6 101x = External RC oscillator, CLKO function on RA6 1001 = Internal RC oscillator, CLKO function on RA6, port function on RA7 1000 = Internal RC oscillator, port function on RA6, port function on RA7 0111 = External RC oscillator, port function on RA6 0110 = HS oscillator, PLL is enabled (Clock Frequency = 4 x FOSC1) 0101 = EC oscillator, port function on RA6 0100 = EC oscillator, CLKO function on RA6 0011 = External RC oscillator, CLKO function on RA6 0010 = HS oscillator 0001 = XT oscillator 0000 = LP oscillator
FOSC<3:0>	CONFIG1H	Oscillator Selection bits (PIC18F2455/2550/4455/4550, PIC18F2458/2553/4458/4553 and PIC18F2450/4450 devices only) 111x = HS oscillator, PLL is enabled, HS is used by USB 110x = HS oscillator, HS is used by USB 1011 = Internal oscillator, HS is used by USB 1010 = Internal oscillator, XT is used by USB 1001 = Internal oscillator, CLKO function on RA6, EC is used by USB 1000 = Internal oscillator, port function on RA6, EC is used by USB 0111 = EC oscillator, PLL is enabled, CLKO function on RA6, EC is used by USB 0110 = EC oscillator, PLL is enabled, port function on RA6, EC is used by USB 0101 = EC oscillator, CLKO function on RA6, EC is used by USB 0100 = EC oscillator, port function on RA6, EC is used by USB 010x = XT oscillator, PLL is enabled, XT is used by USB 000x = XT oscillator, XT is used by USB
USBDIV	CONFIG1L	USB Clock Selection bit (PIC18F2455/2550/4455/4550, PIC18F2458/2553/4458/4553 and PIC18F2450/4450 devices only) Selects the clock source for full-speed USB operation: 1 = USB clock source comes from the 96 MHz PLL divided by 2 0 = USB clock source comes directly from the OSC1/OSC2 oscillator block; no divide
CPUDIV<1:0>	CONFIG1L	CPU System Clock Selection bits (PIC18F2455/2550/4455/4550, PIC18F2458/2553/4458/4553 and PIC18F2450/4450 devices only) 11 = CPU system clock divided by 4 10 = CPU system clock divided by 3 01 = CPU system clock divided by 2 00 = No CPU system clock divide

Note 1: The BBSIZ bits, BBSIZ<1:0> and BBSIZ<2:1> bits, cannot be changed once any of the following code-protect bits are enabled: CPB or CP0, WRTB or WRT0, EBTRB or EBTR0.

2: Not available in PIC18FXX8X and PIC18F2450/4450 devices.

TABLE 5-5: CONFIGURATION WORD MASKS FOR COMPUTING CHECKSUMS

TABLE 5-5:	: CONFIGURATION WORD MASKS FOR COMPUTING CHECKSUMS													
	Configuration Word (CONFIGxx)													
Davisa	1L	1H	2L	2H	3L	3H	4L	4H	5L	5H	6L	6H	7L	7H
Device	Address (30000xh)													
	0h	1h	2h	3h	4h	5h	6h	7h	8h	9h	Ah	Bh	Ch	Dh
PIC18F2221	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F2321	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F2410	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F2420	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F2423	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F2450	3F	CF	3F	1F	00	86	ED	00	03	40	03	60	03	40
PIC18F2455	3F	CF	3F	1F	00	87	E5	00	07	C0	07	E0	07	40
PIC18F2458	3F	CF	3F	1F	00	87	E5	00	07	C0	07	E0	07	40
PIC18F2480	00	CF	1F	1F	00	86	D5	00	03	C0	03	E0	03	40
PIC18F2510	00	1F	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2515	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2520	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2523	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2525	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2550	3F	CF	3F	1F	00	87	E5	00	0F	C0	0F	E0	0F	40
PIC18F2553	3F	CF	3F	1F	00	87	E5	00	0F	C0	0F	E0	0F	40
PIC18F2580	00	CF	1F	1F	00	86	D5	00	0F	C0	0F	E0	0F	40
PIC18F2585	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F2610	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2620	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2680	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F2682	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40
PIC18F2685	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40
PIC18F4221	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F4321	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F4410	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F4420	00	CF CF	1F 1F	1F 1F	00	87 87	C5	00	03	C0	03	E0 E0	03	40 40
PIC18F4423 PIC18F4450	00 3F	CF	3F	1F	00		C5	00	03	C0	03		03	40
PIC18F4455	3F	CF	3F	1F	00	86 87	ED E5	00	03 07	40 C0	03 07	60 E0	03 07	40
PIC18F4458	3F	CF	3F	1F	00	87	E5	00	07	CO	07	E0	07	40
PIC18F4480	00	CF	1F	1F	00	86	D5	00	03	CO	03	E0	03	40
PIC18F4510	00	CF	1F	1F	00	87	C5	00	05 0F	CO	05 0F	E0	05 0F	40
PIC18F4515	00	CF	1F	1F	00	87	C5	00	0F	CO	0F	E0	0F	40
PIC18F4515	00	CF	1F	1F	00	87	C5	00	0F	CO	0F	E0	0F	40
PIC18F4523	00	CF	1F	1F	00	87	C5	00	0F	CO	0F	E0	0F	40
PIC18F4525	00	CF	1F	1F	00	87	C5	00	0F	CO	0F	E0	0F	40
PIC18F4550	3F	CF	3F	1F	00	87	E5	00	0F	CO	0F	E0	0F	40
PIC18F4553	3F	CF	3F	1F	00	87	E5	00	0F	CO	0F	E0	0F	40
PIC18F4580	00	CF	1F	1F	00	86	D5	00	0F	CO	0F	E0	0F	40
PIC18F4585	00	CF	1F	1F	00	86	C5	00	0F	CO	0F	E0	0F	40
PIC18F4610	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
		olle ere i			00	L 01	00	- 00	OI.	- 00	_ U		UI.	70

Legend: Shaded cells are unimplemented.

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY TEST MODE

Standard Operating Conditions

Operating Temperature: 25°C is recommended

Operat	ing rem	perature: 25°C is recommended	<u> </u>	1	1	i		
Param No.	Sym	Characteristic	Min	Max	Units	Conditions		
D110	VIHH	High-Voltage Programming Voltage on MCLR/Vpp/RE3	VDD + 4.0	12.5	V	(Note 2)		
D110A	VIHL	Low-Voltage Programming Voltage on MCLR/VPP/RE3	2.00	5.50	V	(Note 2)		
D111	VDD	Supply Voltage During Programming	2.00	5.50	V	Externally timed, Row Erases and all writes		
			3.0	5.50	V	Self-timed, Bulk Erases only (Note 3)		
D112	IPP	Programming Current on MCLR/VPP/RE3	_	300	μΑ	(Note 2)		
D113	IDDP	Supply Current During Programming	_	10	mA			
D031	VIL	Input Low Voltage	Vss	0.2 VDD	V			
D041	VIH	Input High Voltage	0.8 VDD	VDD	V			
D080	Vol	Output Low Voltage	_	0.6	V	IOL = 8.5 mA @ 4.5V		
D090	Vон	Output High Voltage	VDD - 0.7	_	V	IOH = -3.0 mA @ 4.5V		
D012	Сю	Capacitive Loading on I/O pin (PGD)	_	50	pF	To meet AC specifications		
	•							
P1	TR	MCLR/VPP/RE3 Rise Time to Enter Program/Verify mode	_	1.0	μS	(Notes 1, 2)		
P2	TPGC	Serial Clock (PGC) Period	100	_	ns	VDD = 5.0V		
			1	_	μS	VDD = 2.0V		
P2A	TPGCL	Serial Clock (PGC) Low Time	40	_	ns	VDD = 5.0V		
			400	_	ns	VDD = 2.0V		
P2B	TPGCH	Serial Clock (PGC) High Time	40	_	ns	VDD = 5.0V		
			400	_	ns	VDD = 2.0V		
P3	TSET1	Input Data Setup Time to Serial Clock ↓	15	_	ns			
P4	THLD1	Input Data Hold Time from PGC ↓	15	_	ns			
P5	TDLY1	Delay Between 4-Bit Command and Command Operand	40	_	ns			
P5A	TDLY1A	Delay Between 4-Bit Command Operand and Next 4-Bit Command	40	_	ns			
P6	TDLY2	Delay Between Last PGC ↓ of Command Byte to First PGC ↑ of Read of Data Word	20	_	ns			
P9	TDLY5	PGC High Time (minimum programming time)	1	_	ms	Externally timed		
P10	TDLY6	PGC Low Time After Programming (high-voltage discharge time)	100	_	μS			
P11	TDLY7	Delay to Allow Self-Timed Data Write or Bulk Erase to Occur	5	_	ms			

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH. This can cause spurious program executions to occur. The maximum transition time is:

¹ TCY + TPWRT (if enabled) + 1024 Tosc (for LP, HS, HS/PLL and XT modes only) +

² ms (for HS/PLL mode only) + 1.5 μ s (for EC mode only)

where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and ToSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

^{2:} When ICPRT = 1, this specification also applies to ICVPP.

^{3:} At 0°C-50°C.

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY TEST MODE (CONTINUED)

Standard Operating Conditions Operating Temperature: 25°C is recommended **Param** Sym Characteristic Min Max Units Conditions No. P11A Data Write Polling Time **T**DRWT 4 ms Input Data Hold Time from MCLR/VPP/RE3 ↑ P12 THLD2 2 μS VDD ↑ Setup Time to MCLR/VPP/RE3 ↑ P13 TSET2 100 (Note 2) ns P14 TVALID Data Out Valid from PGC ↑ 10 ns P15 TSET3 PGM ↑ Setup Time to MCLR/VPP/RE3 ↑ 2 (Note 2) цS Delay Between Last PGC ↓ and MCLR/VPP/RE3 ↓ P16 TDLY8 0 s THLD3 MCLR/VPP/RE3 ↓ to VDD ↓ 100 ns P18 MCLR/VPP/RE3 ↓ to PGM ↓ 0 THLD4

1 TCY + TPWRT (if enabled) + 1024 ToSC (for LP, HS, HS/PLL and XT modes only) +

where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and ToSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

- 2: When ICPRT = 1, this specification also applies to ICVPP.
- 3: At 0°C-50°C.

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH. This can cause spurious program executions to occur. The maximum transition time is:

² ms (for HS/PLL mode only) + 1.5 μ s (for EC mode only)